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Team Nexperia



60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor Rev. 1 — 19 May 2010

**Product data sheet** 

#### 1. **Product profile**

### **1.1 General description**

NPN low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

PNP complement: PBSS5560PA.

### 1.2 Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

### 1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	60	V
I <sub>C</sub>	collector current		-	-	6	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 ms$	-	-	7	A
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = 6 A; I <sub>B</sub> = 300 mA	<u>[1]</u> -	34	48	mΩ

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

## 2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	3	3
3	collector		
		1 2	sym021
		Transparent top view	

### 3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PBSS4560PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body 2 $\times$ 2 $\times$ 0.65 mm	SOT1061	

### 4. Marking

Table 4.	Marking codes	
Type num	ber	Marking code
PBSS456	)PA	A8

### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	6	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 ms$	-	7	A
I <sub>B</sub>	base current		-	600	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	500	mW
			[2] _	1	W
			[3] _	1.4	W
			[4] _	2.1	W

#### 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

#### Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

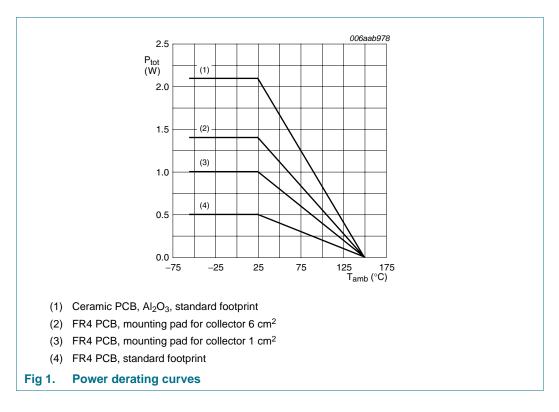
Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	<sub>a)</sub> thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	250	K/W
			[2] _	-	125	K/W
			[3] _	-	90	K/W
			[4]	-	60	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

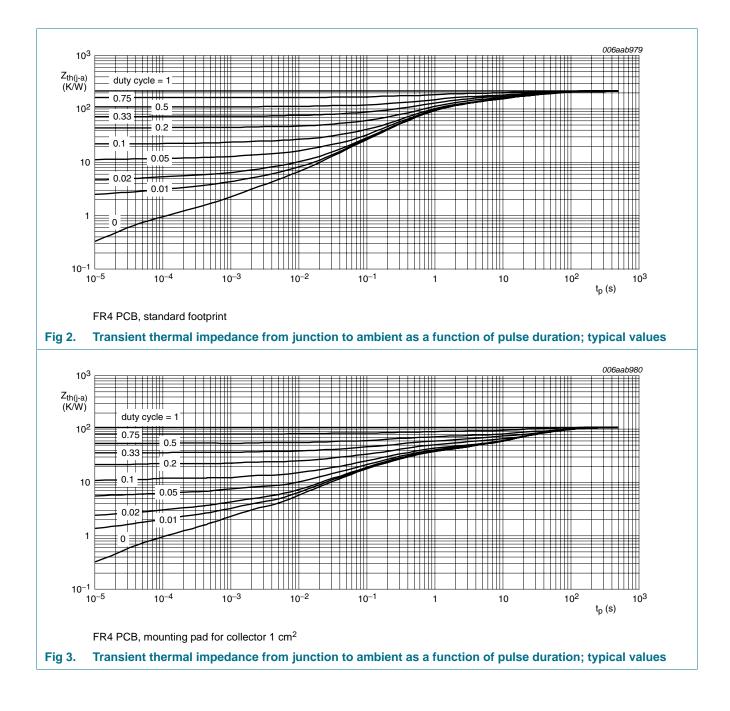
PBSS4560PA

**Product data sheet** 

### **NXP Semiconductors**

# PBSS4560PA

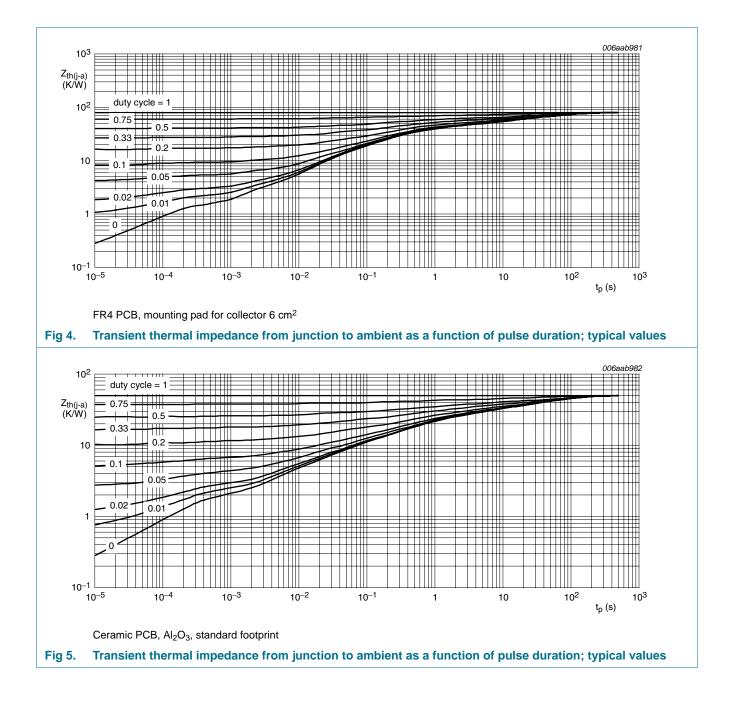
#### 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor



### **NXP Semiconductors**

# PBSS4560PA

#### 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor



60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

### 7. Characteristics

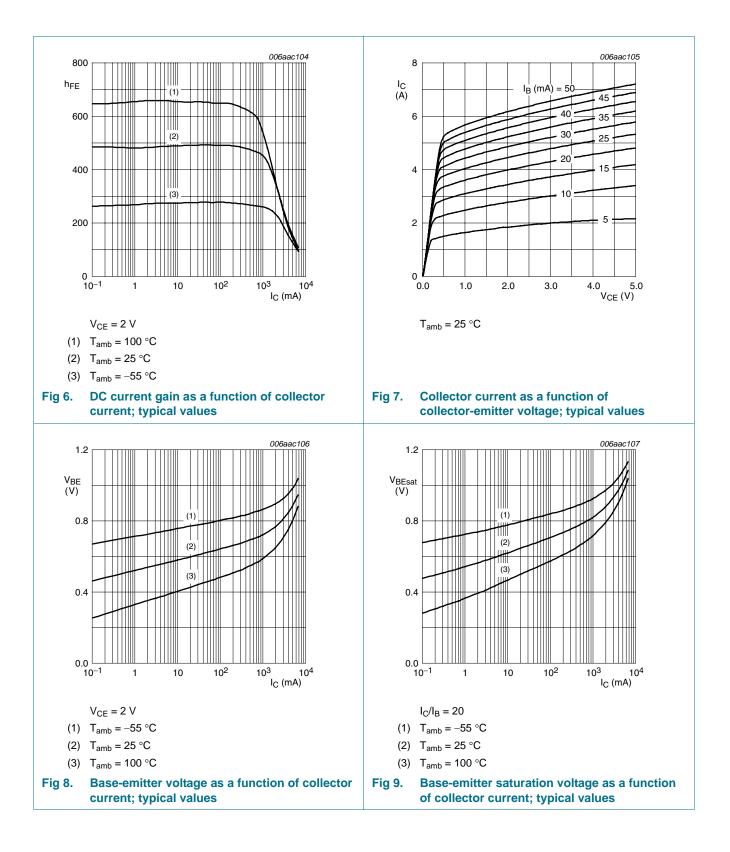
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base	$V_{CB} = 48 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
	cut-off current	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = 48 \text{ V};  V_{BE} = 0 \text{ V}$	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 2 V$	<u>[1]</u>			
		I <sub>C</sub> = 0.5 A	280	440	-	
		I <sub>C</sub> = 1 A	260	420	-	
		I <sub>C</sub> = 2 A	210	325	-	
		I <sub>C</sub> = 6 A	70	120	-	
OLGUI	collector-emitter	$I_{C} = 0.5 \text{ A}; I_{B} = 50 \text{ mA}$	<u>[1]</u> -	22	30	mV
	saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 50 mA	<u>[1]</u> -	45	60	mV
		I <sub>C</sub> = 1 A; I <sub>B</sub> = 10 mA	<u>[1]</u> -	70	95	mV
		$I_{C} = 2 \text{ A}; I_{B} = 20 \text{ mA}$	<u>[1]</u> -	115	170	mV
		I <sub>C</sub> = 3 A; I <sub>B</sub> = 30 mA	<u>[1]</u> -	165	250	mV
		$I_{C} = 4 \text{ A}; I_{B} = 400 \text{ mA}$	<u>[1]</u> -	130	200	mV
		$I_{C} = 6 \text{ A}; I_{B} = 300 \text{ mA}$	<u>[1]</u> -	200	290	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = 6 A; I <sub>B</sub> = 300 mA	<u>[1]</u> _	34	48	mΩ
V <sub>BEsat</sub>	base-emitter	I <sub>C</sub> = 1 A; I <sub>B</sub> = 10 mA	<u>[1]</u> _	0.75	0.9	V
	saturation voltage	I <sub>C</sub> = 6 A; I <sub>B</sub> = 300 mA	<u>[1]</u> _	0.97	1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; I_{C} = 2 \text{ A}$	<u>[1]</u> _	0.75	0.9	V
t <sub>d</sub>	delay time	$V_{CC} = 9 V; I_C = 2 A;$	-	22	-	ns
t <sub>r</sub>	rise time	I <sub>Bon</sub> = 0.1 A; I <sub>Boff</sub> = -0.1 A	-	101	-	ns
t <sub>on</sub>	turn-on time		-	123	-	ns
t <sub>s</sub>	storage time		-	635	-	ns
t <sub>f</sub>	fall time		-	145	-	ns
t <sub>off</sub>	turn-off time		-	780	-	ns
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 100 mA; f = 100 MHz	90	150	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	23	30	pF

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### **NXP Semiconductors**

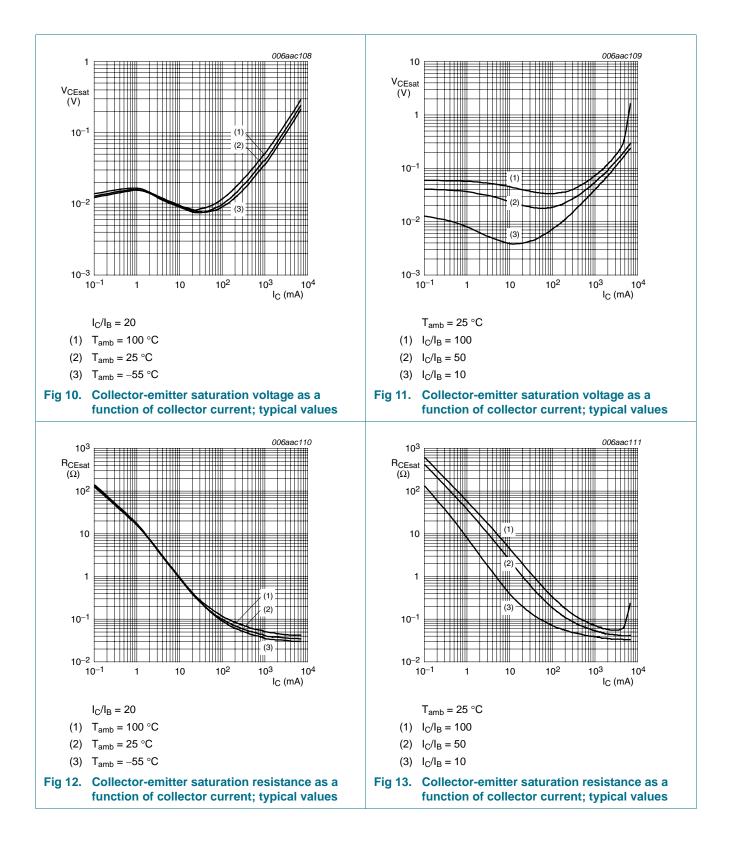
# PBSS4560PA

#### 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor



PBSS4560PA

#### 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

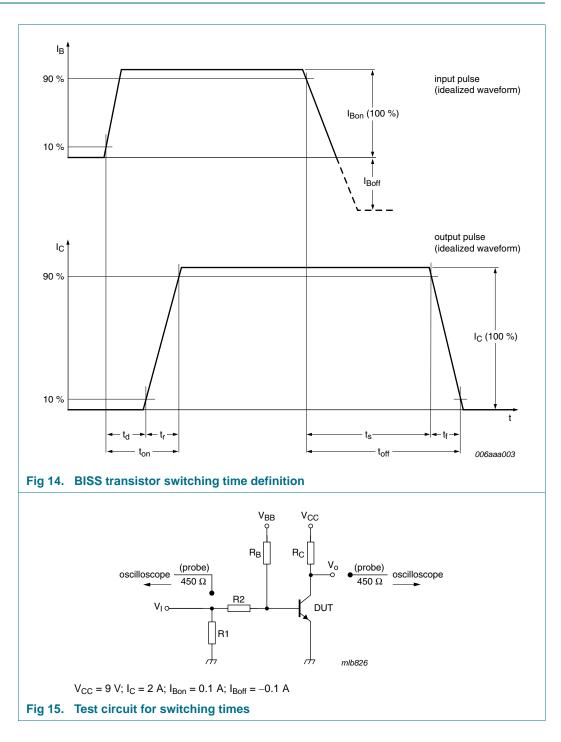


PBSS4560PA

Product data sheet

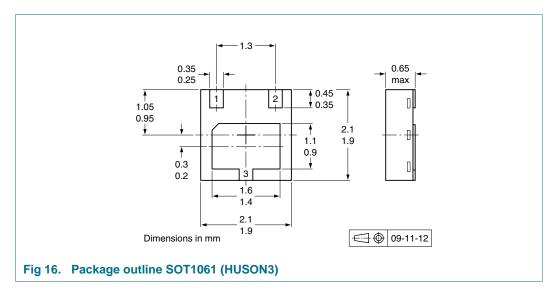
60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

### 8. Test information



60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

### 9. Package outline



### **10. Packing information**

#### Table 8. Packing methods

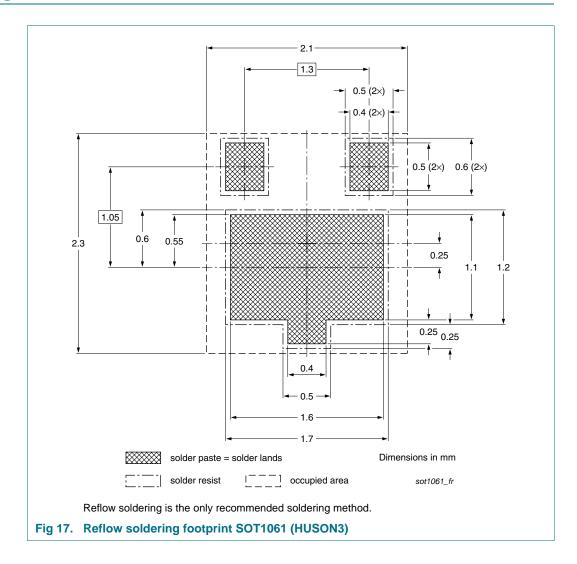
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number Packa	ige Description	Packing quantity 3000
PBSS4560PA SOT1	061 4 mm pitch, 8 mm tape and reel	-115

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

### 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

### 11. Soldering



PBSS4560PA

60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

# **12. Revision history**

Table 9. Revision hist	Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS4560PA v.1	20100519	Product data sheet	-	-	

#### 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

### 13. Legal information

### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PBSS4560PA

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#### 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

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### 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

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